5/22/06 AU 2811 OK to Enter

AMENDMENTS TO THE CLAIMS:

This listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Currently Amended) A method for fabricating a thin film transistor, comprising:

forming a first amorphous semiconductor film;

forming a material including a metal element to promote crystallization over the first amorphous semiconductor film;

heating the first amorphous semiconductor film to form a first crystalline semiconductor film;

forming a second amorphous semiconductor film over the first crystalline semiconductor film;

heating the first crystalline semiconductor film and the second amorphous semiconductor film; and

removing the second amorphous semiconductor film[[; and]].

wherein the second amorphous semiconductor film serves as a gettering sink, and

wherein the second amorphous semiconductor film comprises nitrogen at a concentration of 1×10^{18} atoms/cm^3 or lower, oxygen at a concentration of 8×10^{19} atoms/cm^3 or lower, and noble gas at a concentration of 1×10^{20} atoms/cm^3 or higher.

2. (Withdrawn) A method for fabricating a thin film transistor, comprising:

forming a first amorphous semiconductor film;

forming a material including a metal element to promote crystallization over the first amorphous semiconductor film;

forming a first crystalline semiconductor film by heating the first amorphous semiconductor film;

irradiating the first crystalline semiconductor film with a laser beam;

forming a second amorphous semiconductor film over the first crystalline semiconductor film;

heating the first crystalline semiconductor film and the second amorphous